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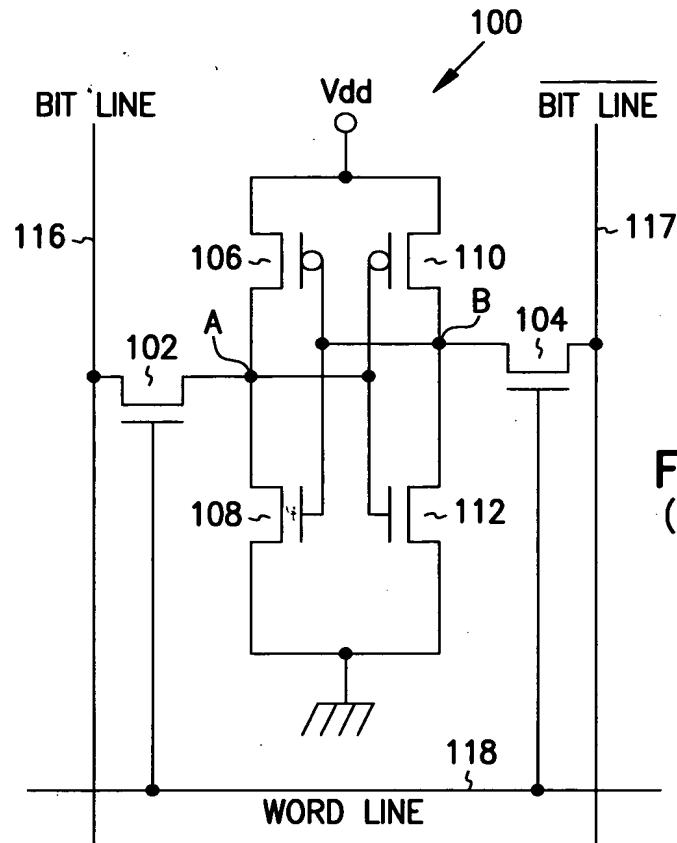


FIG. 1A
(PRIOR ART)

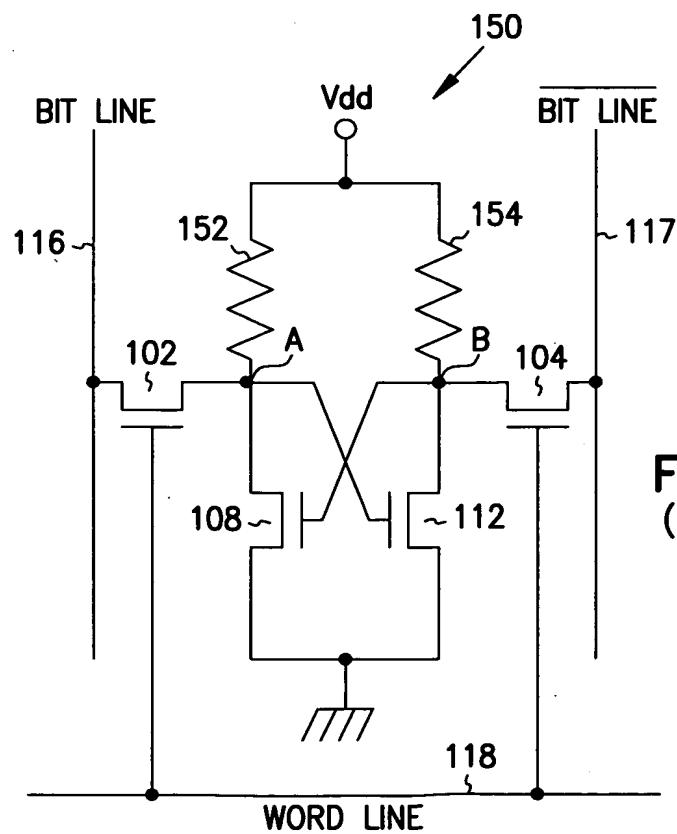


FIG. 1B
(PRIOR ART)

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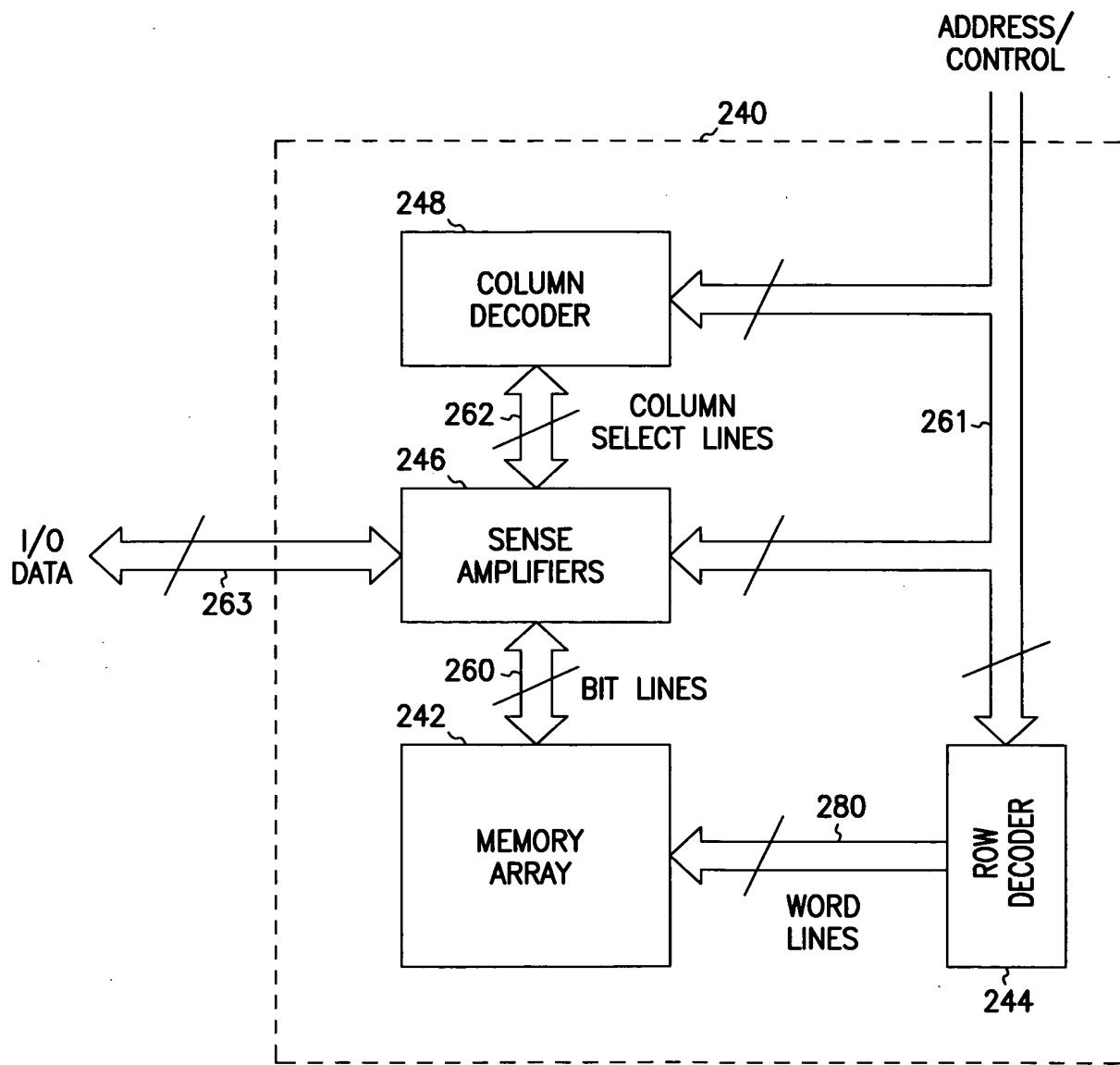


FIG. 2

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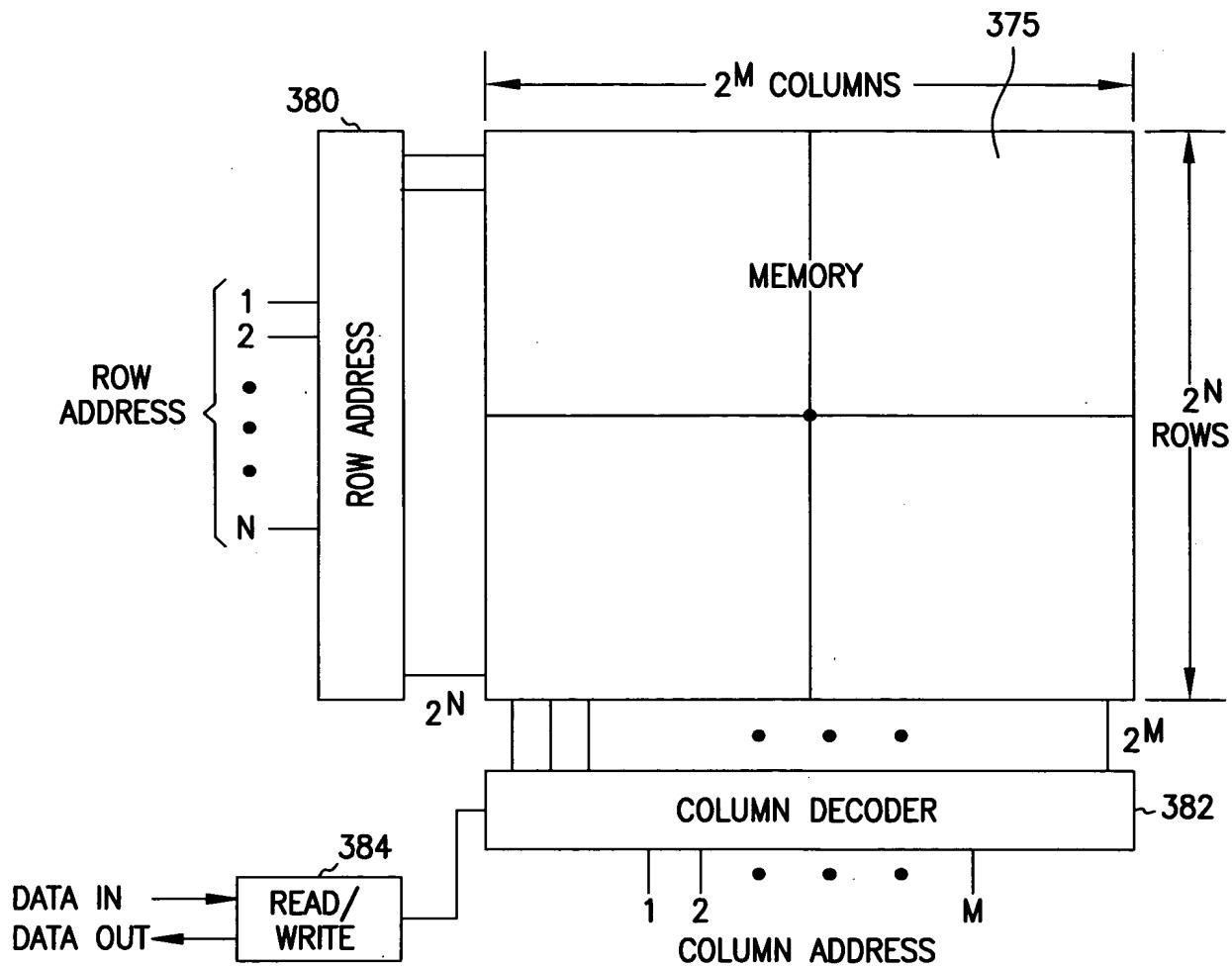


FIG. 3

TITLE: SRAM CELLS WITH RECESSED FLOATING GATE MEMORY, LOW TUNNEL BARRIER INTERPOLY
INSULATORS
INVENTORS NAME: Leonard Forbes
DOCKET NO.: 1303.028US1

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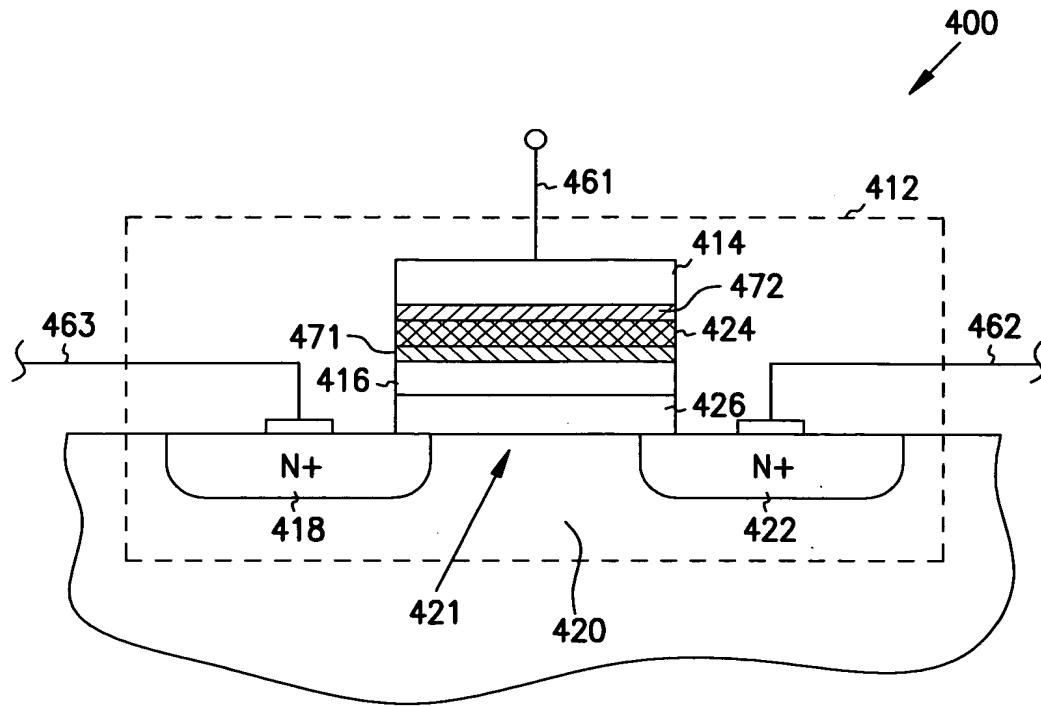


FIG. 4

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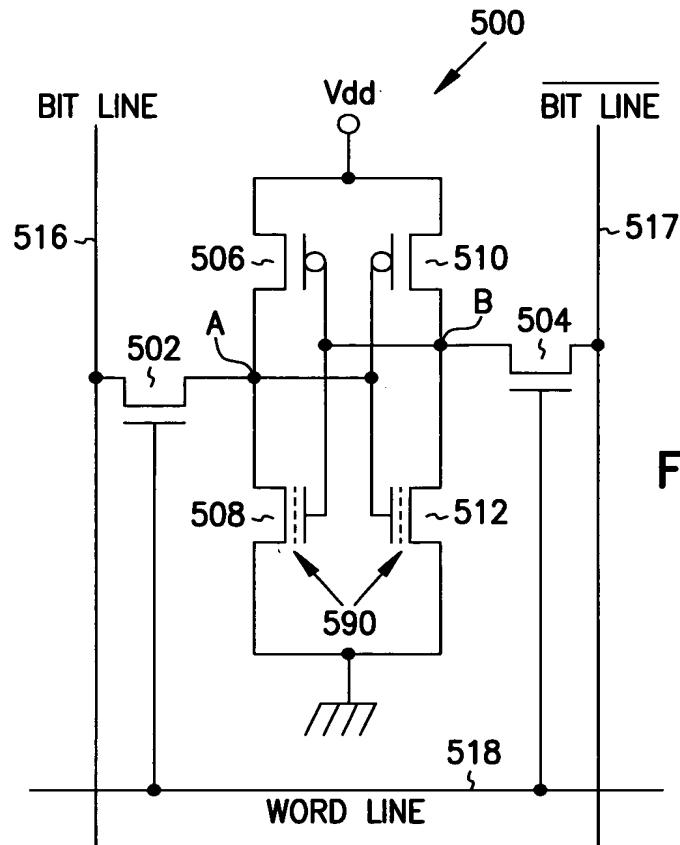


FIG. 5A

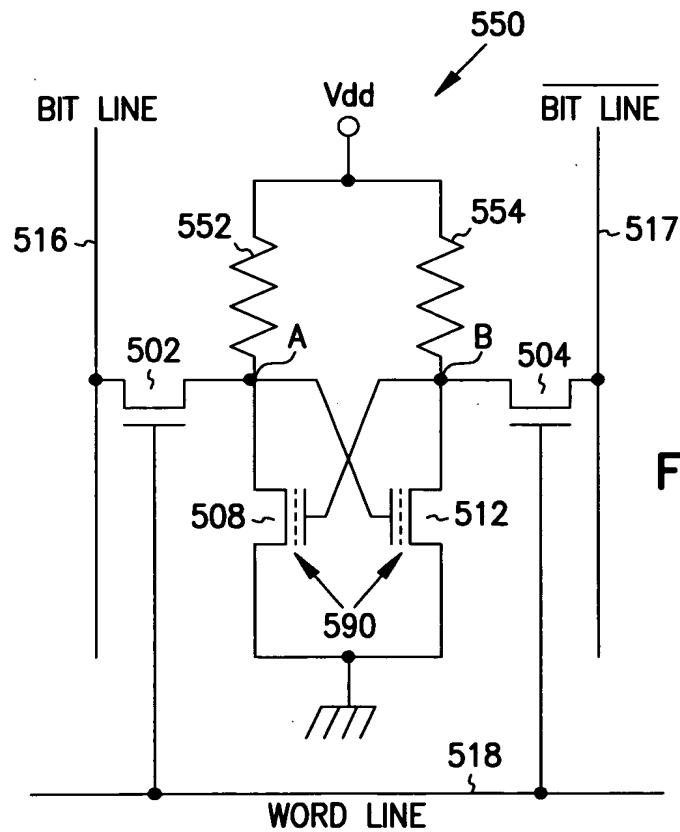


FIG. 5B

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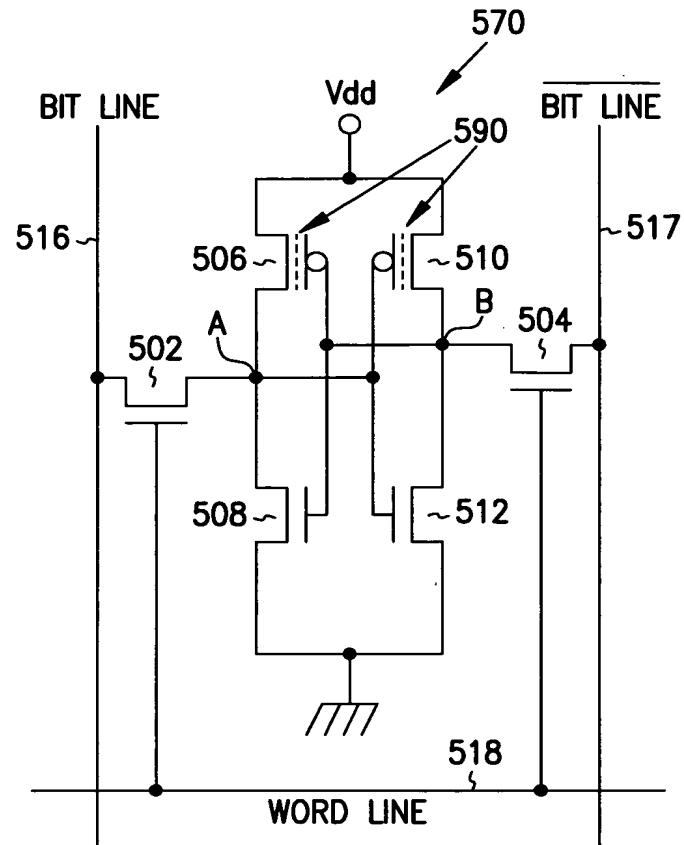


FIG. 5C

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FIGURE 6A

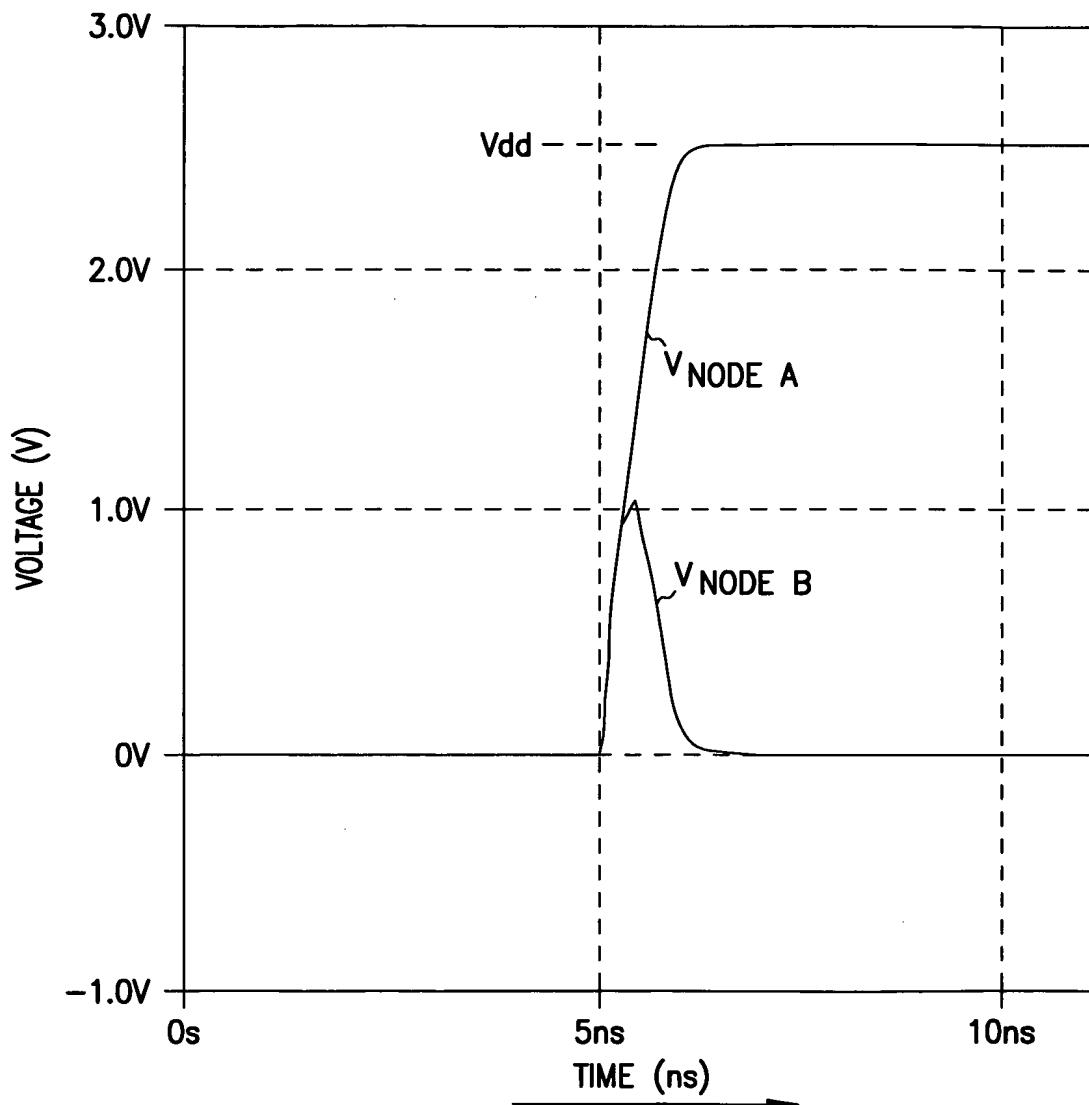


FIG. 6A

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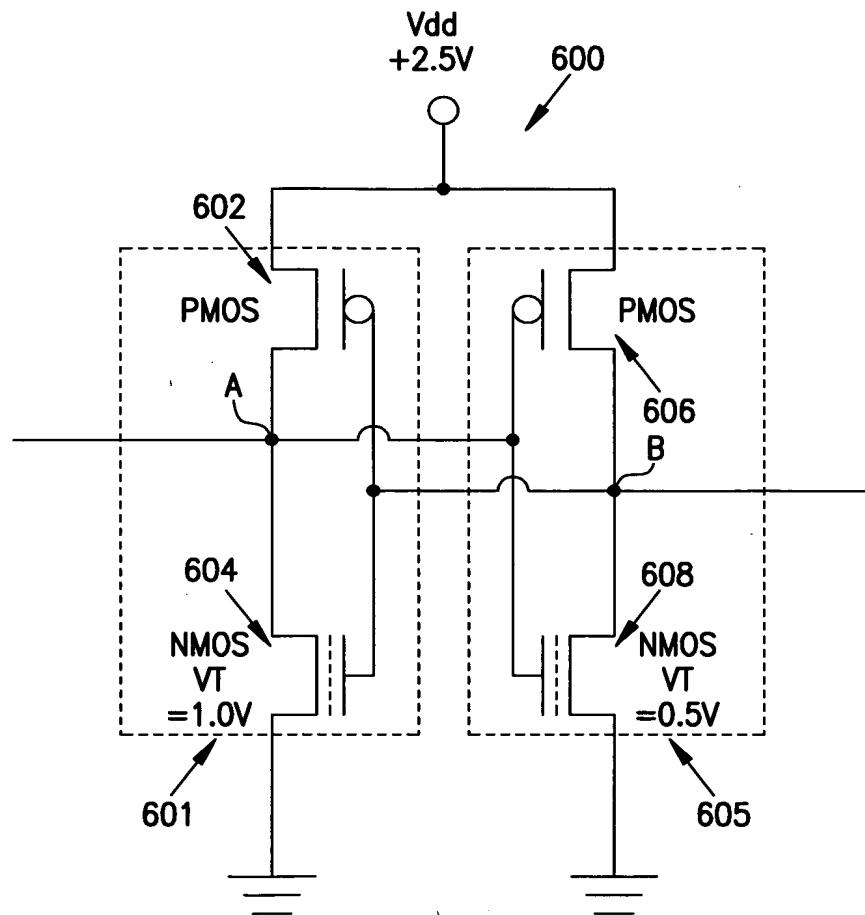


FIG. 6B

TITLE: SRAM CELLS WITH RAPIDLY DOPED FLOWING GATE MEMORY, LOW TUNNEL BARRIER INTERPOLY
INSULATORS

INVENTORS NAME: Leonard Forbes
DOCKET NO.: 1303.028US1

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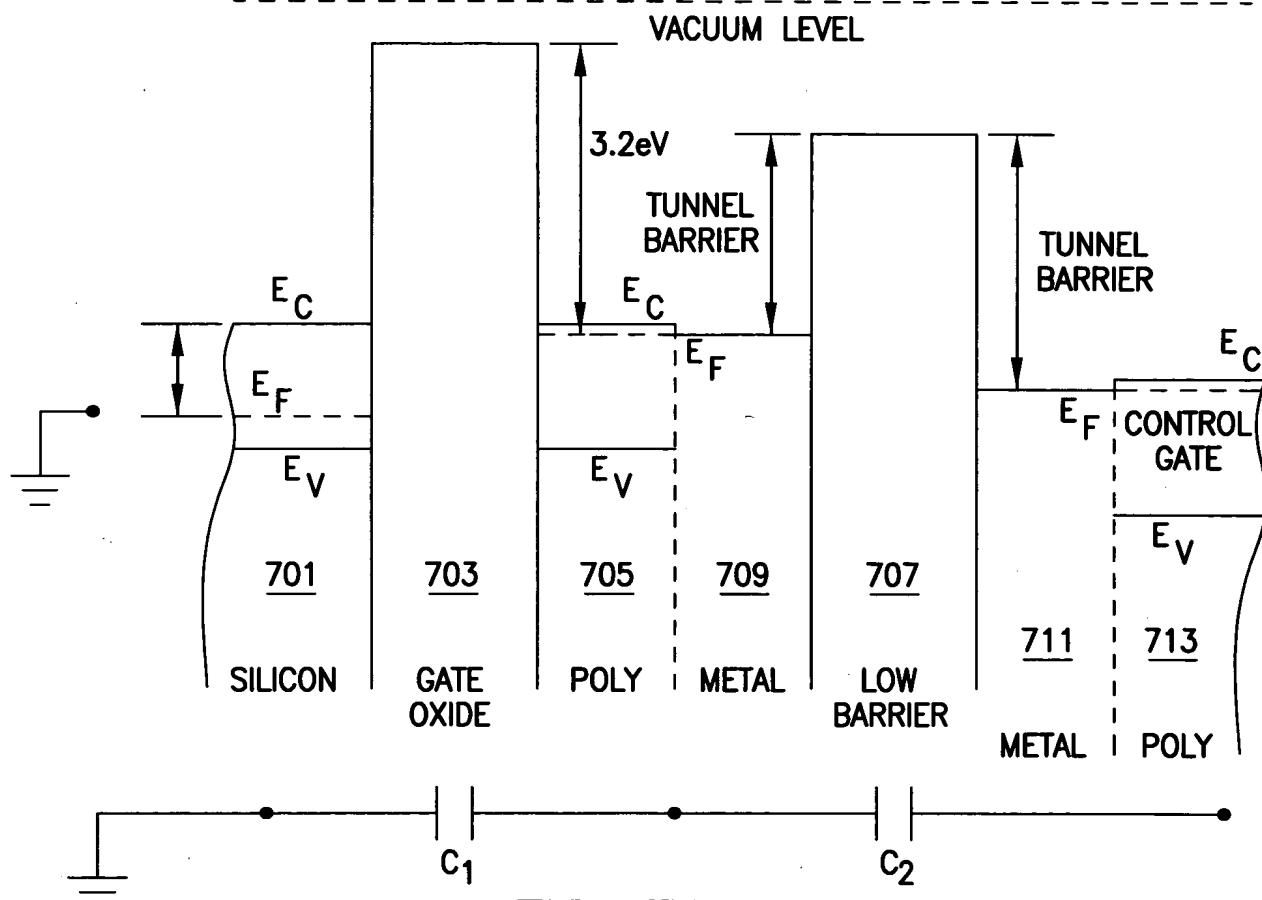
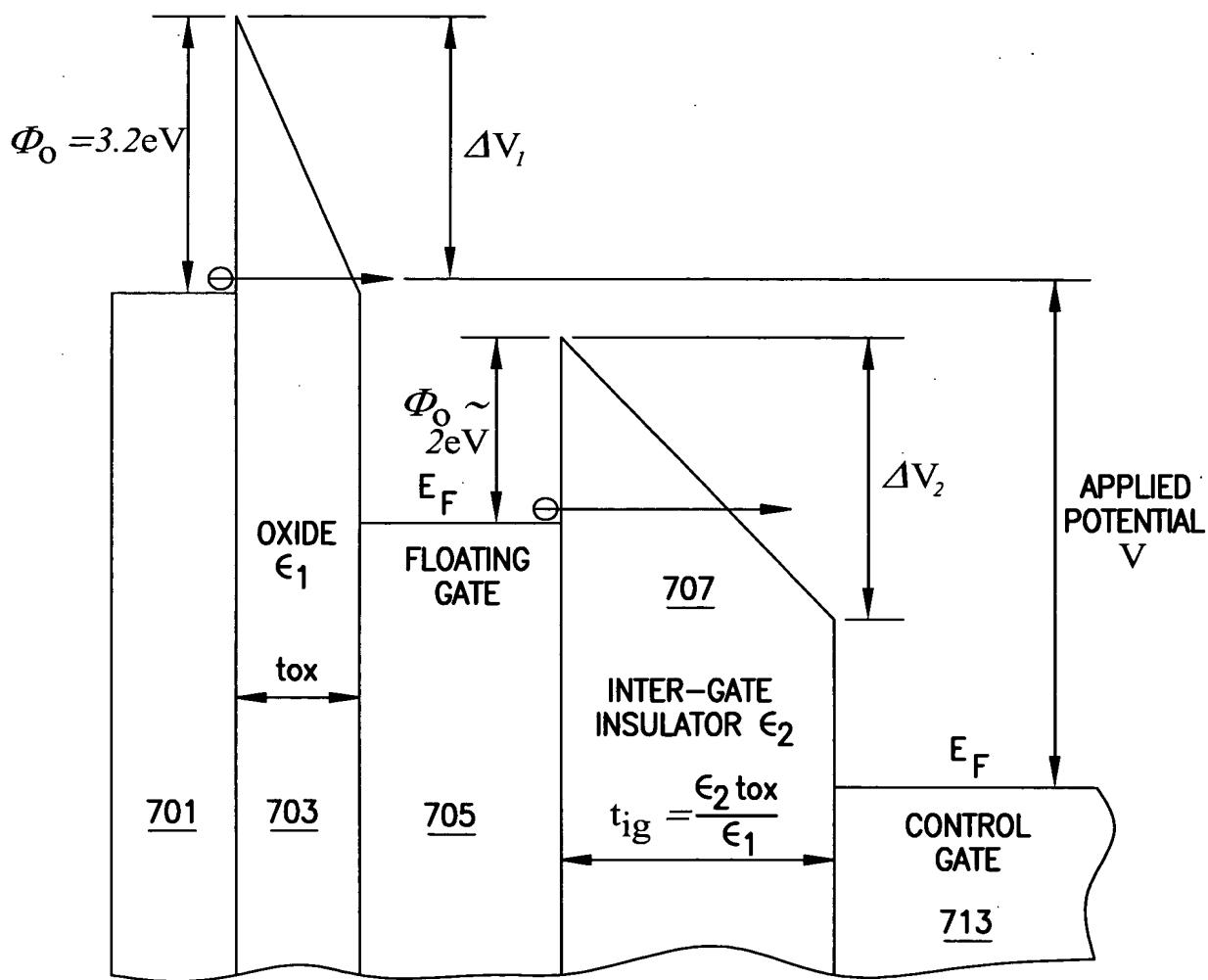


FIG. 7A

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$$J = \frac{q^2 E^2 - E_0/E}{4\pi h \Phi} e \quad E_0 = \frac{8\pi}{3} \sqrt{\frac{2m^*}{h}} \Phi^{3/2}$$

FIG. 7B

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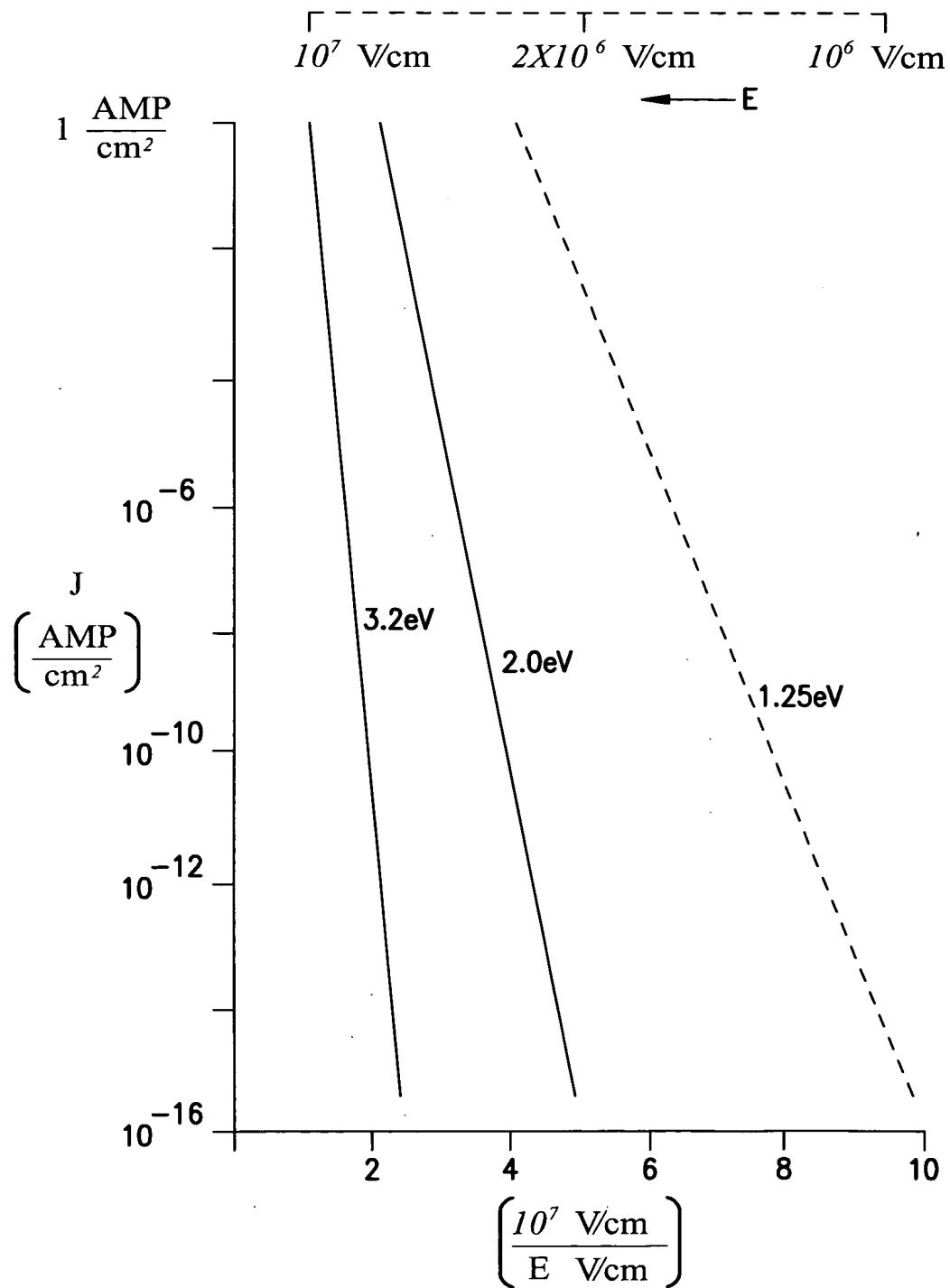


FIG. 7C

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PROSECUTOR'S FILE NUMBER 0882001

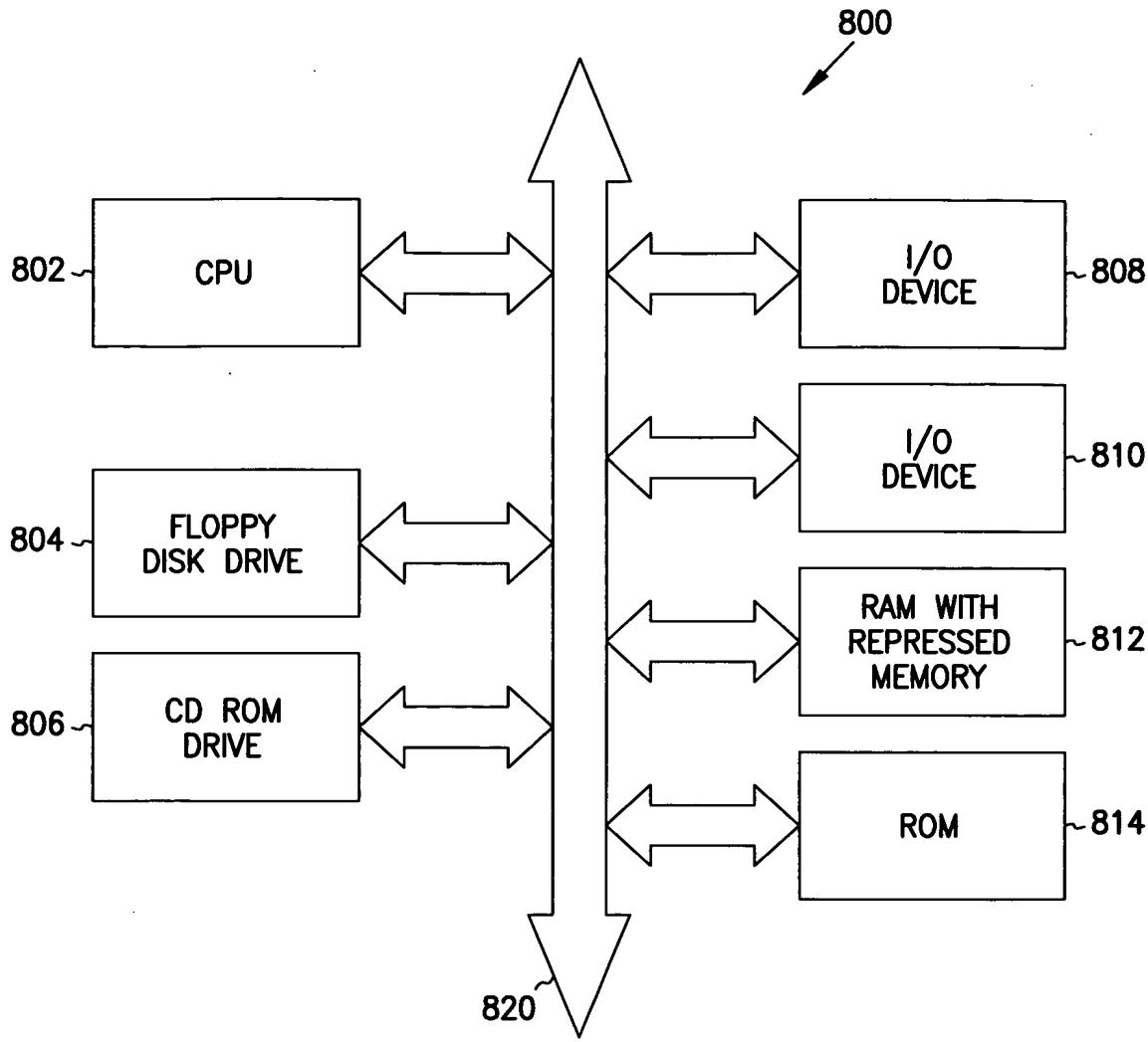


FIG. 8